

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

Applicants: J. YUGAMI, et al.

Application No.: Rule 1.53(b) Divisional of U.S. Patent Application Serial No. 10/005,355, filed December 7, 2001

Filed: On Even Date Herewith

For: SEMICONDUCTOR DEVICE AND PROCESS FOR PRODUCING THE SAME

Art Group of Parent: 2829

Examiner of Parent: S. B. Geyer

**INFORMATION DISCLOSURE STATEMENT**  
**UNDER 37 CFR §1.97 & 1.98**

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

February 12, 2004

Sir:

In the matter of the above-identified application, this Information Disclosure Statement is being submitted with the following citation as specified in 37 CFR §1.97(d).

"A copy of any patent, publication or other information listed in an Information Disclosure Statement is not required to be provided if it was previously cited by or submitted to the Office in a prior application, provided that the prior application is properly identified in the statement and relied upon for an earlier filing date under 35 U.S.C. §120."

Applicants are submitting herewith a copy of Form PTO/SB/08A which list documents cited in parent application Serial No. 10/005,355, filed December 7, 2001, the entire disclosure of which is hereby incorporated by reference.

It is respectfully requested that this information disclosure statement be considered by the Examiner.

To the extent necessary, the applicants petition for an extension of time under 37 CFR 1.136. Please charge any shortage in the fees due in connection with the filing of this paper, including extension of time fees, to the Antonelli, Terry, Stout & Kraus, Deposit Account No. 01-2135 (Docket No. 520.40885VX1).

Respectfully submitted,

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By



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Substitute for form 1449A/PTO			<b>C mplete if Known</b>	
<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>  (use as many sheets as necessary)			Application Number	Not assigned yet
			Filing Date	On even date herewith
			First Named Inventor	J. YUGAMI, et al.
			Art Unit	Not assigned yet
			Examiner Name	Not assigned yet
Sheet 1 of 1	Attorney Docket Number		520.40885VX1	

U.S. PATENT DOCUMENTS						
Examiner Initials*	Cite No. <sup>1</sup>	Document Number		Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code <sup>2</sup> (if known)				
		6,495,890 B1		12-2002	Ono	
		5,514,891		05-1996	Abrokwhah et al.	

FOREIGN PATENT DOCUMENTS							
Examiner Initials*	Cite No. <sup>1</sup>	Foreign Patent Document		Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T <sup>6</sup>
		Country Code <sup>3</sup> -Number <sup>4</sup> -Kind Code <sup>5</sup> (if known)					
		JP 110003990		1/6/99			

OTHER PRIOR ART—NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published	T <sup>2</sup>
		1998 International Electron Device Meeting Technical Digest, (Pgs. 1038-1040), A 1.1 nm Oxide Equivalent Gate Insulator Formed Using TiO <sub>2</sub> on Nitrided Silicon.	
		IEEE Transactions on Electron Devices, Vol. 46, No. 7, July 1999, (Pages 1537-1544), The Impact of High-k Gate Dielectrics and Metal Gate Electrodes on Sub-100 nm MOSFET's	

Examiner Signature		Date Considered	
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\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

<sup>1</sup>Applicant's unique citation designation number (optional). <sup>2</sup>See Kinds Codes of USPTO Patent Documents at [www.uspto.gov](http://www.uspto.gov) or MPEP 901.04. <sup>3</sup>Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). <sup>4</sup>For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. <sup>5</sup>Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. <sup>6</sup>Applicant is to place a check mark here if English language Translation is attached.

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